PG05NSSMC

Single Line TVS Diode for ESD Protection

Protection of Voltage Sensitive Components.

FEATURES

· Low profile package.

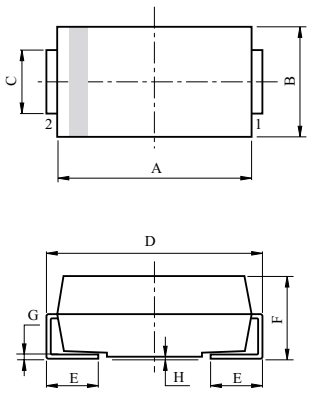
· Transient protection for data line to

APPLICATIONS

· Devices for Unidirectional Applications.

· Automotive Controller.

· Notebooks, Desktops, & Servers.



DIM	MILLIMETERS
A	6.60 ~ 7.11
B	5.59 ~ 6.22
C	2.92 ~ 3.07
D	7.75 ~ 8.13
E	0.76 ~ 1.52
F	2.00 ~ 2.62
G	0.15 ~ 0.31
H	0.10 ~ 0.20

1. ANODE
2. CATHODE

SMC

MAXIMUM RATING (Ta=25℃)

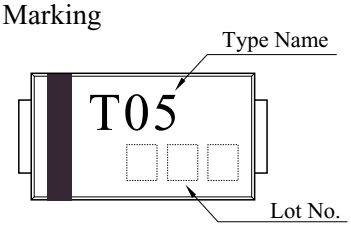
CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Pulse Power (tp=10/1000㎲)	P_{PK}	1500	W
Peak Pulse Current (tp=10/1000㎲)	I_{PP}	163	A
Operating Temperature	T_j	-55～150	℃
Storage Temperature	T_{stg}	-55～150	℃

* Notes) : (1) Derated above Ta=25℃ per power derating curve.

(2) Mounted on 0.31 ×0.31 (8.0 ×8.0㎜) copper pads to each terminal.

(3) Mounted on minimum recommened pad lay out

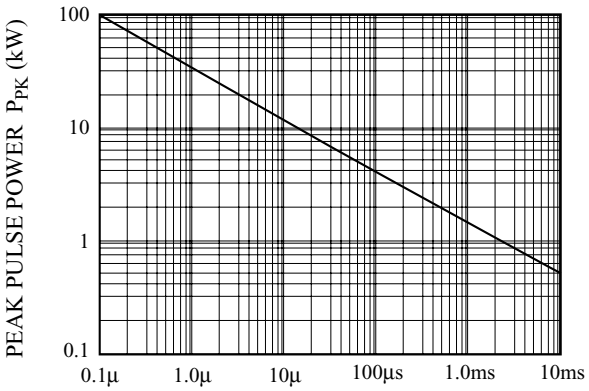
Marking



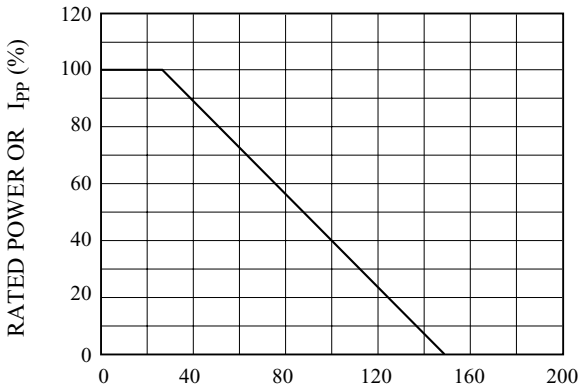
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	I_t=10mA	6.40	-	7.07	V
Reverse Leakage Current	I_R	V_{RWM}=5V	-	-	1000	㎂
Clamping Voltage	V_C	I_{PP}=163A, tp=10/1000㎲	-	-	9.2	V

NON-REPETITIVE PEAK PULSE POWER vs. PULSE TIME



POWER DERATION CURVE



PULSE WAVEFORM

